Docket No.: 60188-589 **PATENT**

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Kaoru INOUE, et al.

Serial No.: 10/620,430

Filed: July 17, 2003

NEC 1 8 2003

Customer Number: 20277

Confirmation Number: 1098

Group Art Unit:

Examiner: Unknown

For: METHOD FOR FABRICATING SEMICONDUCTOR DEVICE

INFORMATION DISCLOSURE STATEMENT

Mail Stop IDS Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Dear Sir:

In accordance with the provisions of 37 C.F.R. 1.56, 1.97 and 1.98, the attention of the Patent and Trademark Office is hereby directed to the documents listed on the attached form PTO-1449. It is respectfully requested that the documents be expressly considered during the prosecution of this application, and that the documents be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

This Information Disclosure Statement is being filed within three months of the U.S. filing date OR before the mailing date of a first Office Action on the merits. No certification or fee is required.

10/620,430

Please charge any shortage in fees due in connection with the filing of this paper, including extension of time fees, to Deposit Account 500417 and please credit any excess fees to such deposit account.

Respectfully submitted,

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Date: December 18, 2003

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INFORMATION DISCLOSURE CITATION IN AN APPLICATION									ERIAL NO. 0/620,430			
PEC 1 8 2003 (PTO-1449)						APPLICANT Kaoru INOUE, et al.						
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		C.F. Lin et al., "Improved Contact Performance of GaN Film Using Si Diffusion:, 2000 American Institute of Physics, Applied Physics Letters, Vo. 76, No. 14, pp. 1878-1880, April 3, 2000									ied	
Hiroyuki MASATO et al., "Novel High Drain Breakdown Voltage AlGaN/GaN HFETs Using Selective Thermal Oxidatio Process", IEEE, IEDM 16.2.1-16.2.4, pp. 377-380, 2000										1		
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^{*}EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

1 Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached.